

Notice of References Cited	Application/Control No. 09/605,293		Applicant(s)/Patent Under Reexamination CHAPEK, DAVID L.	
	Examiner JAY C. KIM		Art Unit 2815	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	K	US-			
	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

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	V	Magnuson et al., "High Efficiency Source for Metal Ions", The Review of Scientific Instruments 36 (1965) pp. 136-142.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.